

BDT91
BDT93
BDT95

SILICON EPITAXIAL BASE POWER TRANSISTORS

N-P-N transistors in a plastic envelope intended for use in audio output stages and general amplifier and switching applications.

P-N-P complements are BDT92, BDT94 and BDT96.

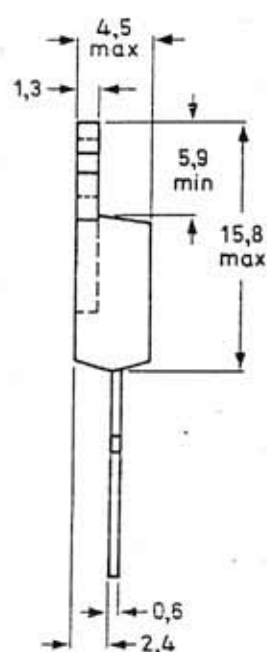
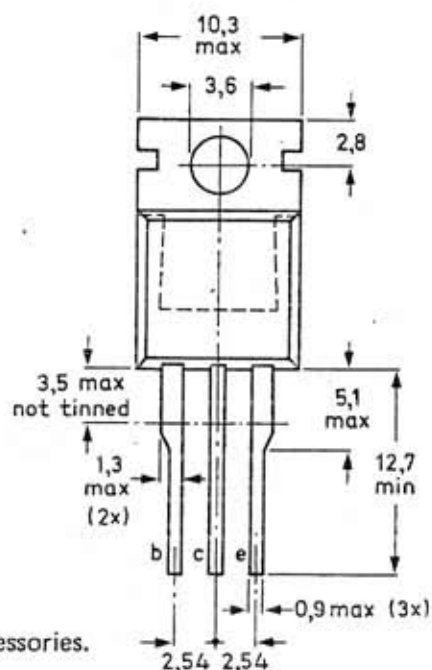
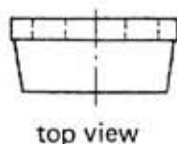
QUICK REFERENCE DATA

			BDT91	BDT93	BDT95
Collector-base voltage (open emitter)	V_{CBO}	max.	60	80	100 V
Collector-emitter voltage (open base)	V_{CEO}	max.	60	80	100 V
Collector current (d.c.)	I_C	max.		10	A
Collector current (peak value)	I_{CM}	max.		20	A
Total power dissipation up to $T_{mb} = 25^\circ\text{C}$	P_{tot}	max.		90	W
Junction temperature	T_j	max.		150	$^\circ\text{C}$
D.C. current gain					
$I_C = 4\text{ A}; V_{CE} = 4\text{ V}$	h_{FE}			20 to 200	
$I_C = 10\text{ A}; V_{CE} = 4\text{ V}$	h_{FE}	>		5	
Transition frequency					
$I_C = 0,5\text{ A}; V_{CE} = 10\text{ V}$	f_T	>		4	MHz

MECHANICAL DATA

Fig. 1 TO-220AB.

Collector connected to mounting base.



See also chapters
Mounting instructions and Accessories.

BDT91
BDT93
BDT95



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BDT91	BDT93	BDT95
Collector-base voltage (open emitter)	V_{CBO}	max.	60	80	100 V
Collector-emitter voltage (open base)	V_{CEO}	max.	60	80	100 V
Emitter-base voltage (open collector)	V_{EBO}	max.		7	V
Collector current (d.c.)	I_C	max.		10	A
Collector current (peak value)	I_{CM}	max.		20	A
Base current (d.c.)	I_B	max.		4	A
Total power dissipation up to $T_{mb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.		90	W
Storage temperature	T_{stg}			-65 to +150	$^{\circ}\text{C}$
Junction temperature	T_j	max.		150	$^{\circ}\text{C}$

THERMAL RESISTANCE

→ From junction to mounting base	$R_{th\ j-mb}$	=		1,4	K/W
From junction to ambient (in free air)	$R_{th\ j-a}$	=		70	K/W

CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Collector cut-off current

$I_E = 0; V_{CB} = V_{CBOmax}$	I_{CBO}	<		0,1	mA
$I_E = 0; V_{CB} = \frac{1}{2}V_{CBOmax}; T_j = 150\text{ }^{\circ}\text{C}$	I_{CBO}	<		5	mA
$I_B = 0; V_{CE} = V_{CEOmax}$	I_{CEO}	<		1	mA

Emitter cut-off current

$I_C = 0; V_{EB} = 7\text{ V}$	I_{EBO}	<		1	mA
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D.C. current gain (note 1)

$I_C = 4\text{ A}; V_{CE} = 4\text{ V}$	h_{FE}			20 to 200	
$I_C = 10\text{ A}; V_{CE} = 4\text{ V}$	h_{FE}	>		5	

Base-emitter voltage (notes 1 and 2)

$I_C = 4\text{ A}; V_{CE} = 4\text{ V}$	V_{BE}	<		1,6	V
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Collector-emitter saturation voltage (note 1)

$I_C = 4\text{ A}; I_B = 0,4\text{ A}$	V_{CEsat}	<		1	V
$I_C = 10\text{ A}; I_B = 3,3\text{ A}$	V_{CEsat}	<		3	V

Transition frequency at $f = 1\text{ MHz}$

$I_C = 0,5\text{ A}; V_{CE} = 10\text{ V}$	f_T	>		4	MHz
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Cut-off frequency

$I_C = 0,5\text{ A}; V_{CE} = 10\text{ V}$	f_{hfe}	>		20	kHz
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Notes

1. Measured under pulse conditions: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 2\%$.
2. V_{BE} decreases by about 2,3 mV/K with increasing temperature.

BDT91
BDT93
BDT95



Second-breakdown collector current

$$V_{CE} = 60 \text{ V}; t_p = 0,1 \text{ s}$$

$$I_{(SB)} > 1,5 \text{ A}$$

Switching times

(between 10% and 90% levels)

$$I_{Con} = 4 \text{ A}; I_{Bon} = -I_{Boff} = 0,4 \text{ A}$$

Turn-on time

$$t_{on} < \begin{matrix} \text{typ.} & 0,5 \mu\text{s} \\ & 1 \mu\text{s} \end{matrix}$$

Turn-off time

$$t_{off} < \begin{matrix} \text{typ.} & 2 \mu\text{s} \\ & 4 \mu\text{s} \end{matrix}$$

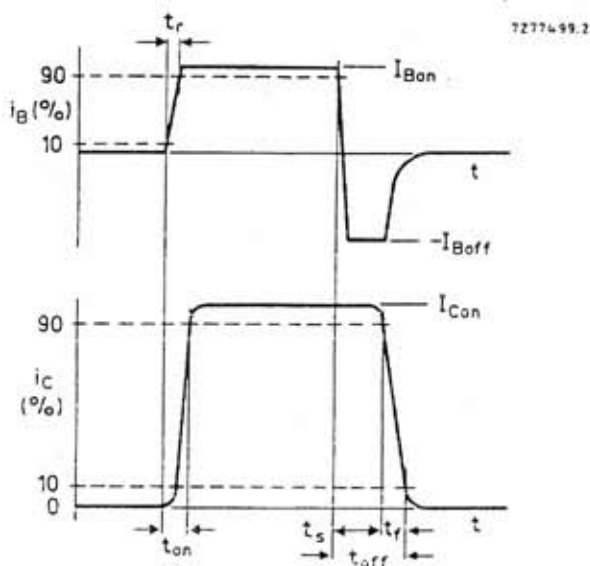


Fig. 2 Switching times waveforms.

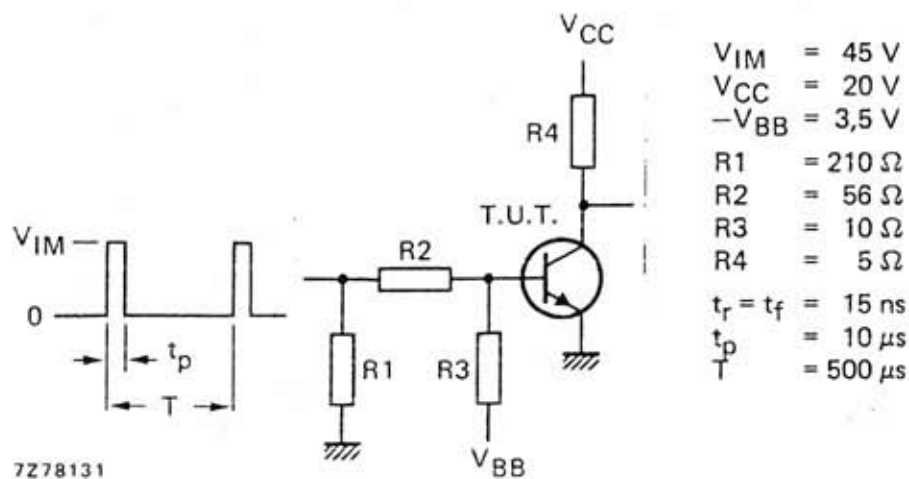


Fig. 3 Switching times test circuit.

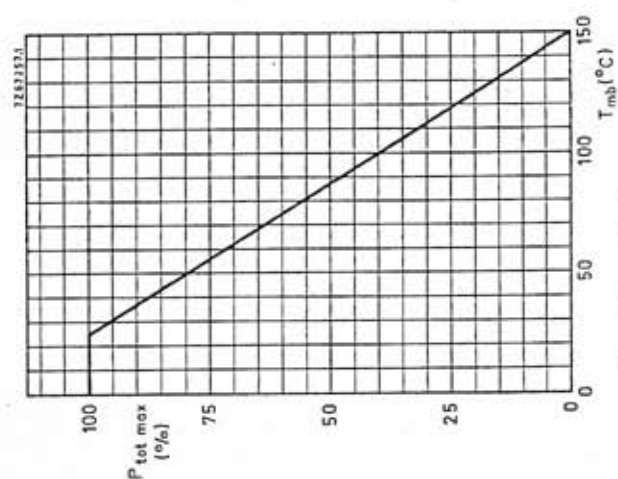


Fig. 5 Power derating curve.

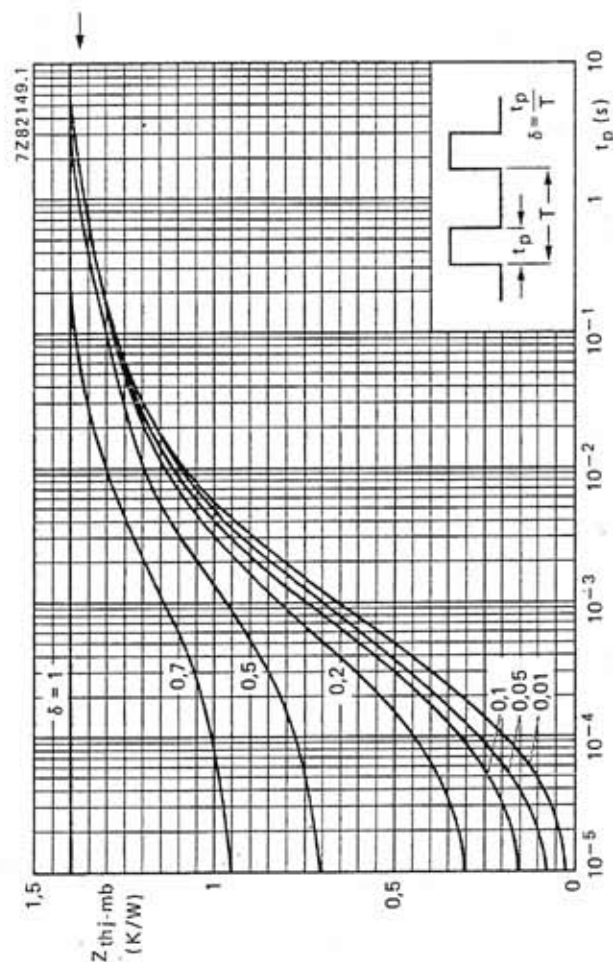


Fig. 6 Pulse power rating chart.

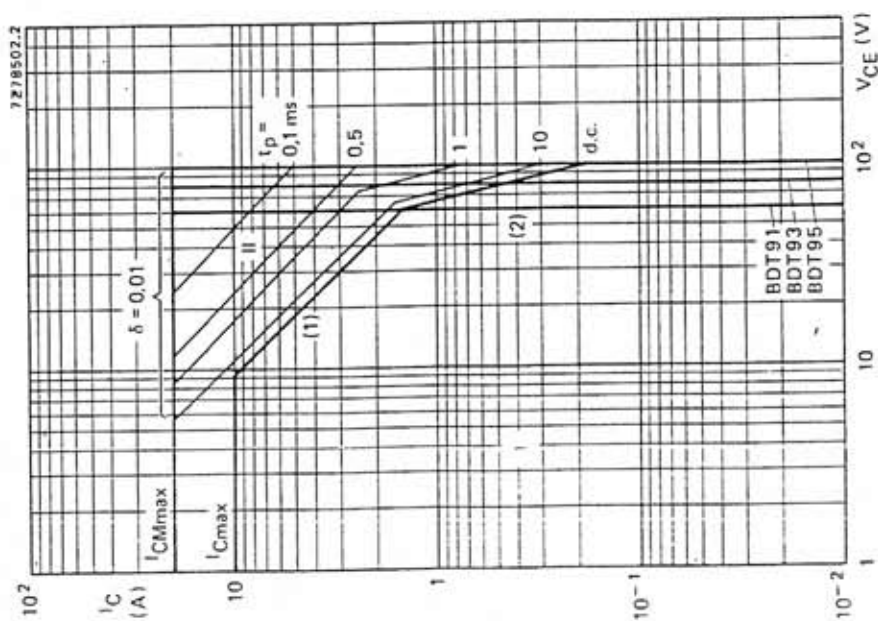


Fig. 4 Safe Operating Area; $T_{mb} = 25^\circ\text{C}$.

I Region of permissible d.c. operation.

II Permissible extension for repetitive pulse operation.

(1) $P_{tot\ max}$ and $P_{peak\ max}$ lines.

(2) Second-breakdown limits (independent of temperature).

